

INFORMATION DISCLOSURE
STATEMENT BY APPLICANT

(use as many sheets as necessary)

Sheet A1 of 1



Complete if Known

Application Number	10772,882
Filing Date	February 5, 2004
First Named Inventor	Sauder
Group Art Unit	2811
Examiner Name	Jerome Jackson, Jr.

Attorney Docket Number 5308-389

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*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.